# MJE2955T (PNP), MJE3055T (NPN)

# Complementary Silicon Plastic Power Transistors

These devices are designed for use in general−purpose amplifier and switching applications.

**Features**

- High Current Gain − Bandwidth Product
- These Devices are Pb−Free and are RoHS Compliant*

**MAXIMUM RATINGS**

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Collector−Emitter Voltage | $V_{CEO}$ | 60 | Vdc |
| Collector−Base Voltage | $V_{CB}$ | 70 | Vdc |
| Emitter−Base Voltage | $V_{EB}$ | 5.0 | Vdc |
| Collector Current | $I_C$ | 10 | Adc |
| Base Current | $I_B$ | 6.0 | Adc |
| Total Device Dissipation<br>@ $T_C$ = 25°C<br>Derate above 25°C | $P_D$<br>(Note 1) | 75<br>0.6 | W<br>W/°C |
| Operating and Storage Junction Temperature Range | $T_J$, $T_{stg}$ | −55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

**THERMAL CHARACTERISTICS**

| Characteristics | Symbol | Max | Unit |
|---|---|---|---|
| Thermal Resistance, Junction−to−Case | $R_{\theta JC}$ | 1.67 | °C/W |

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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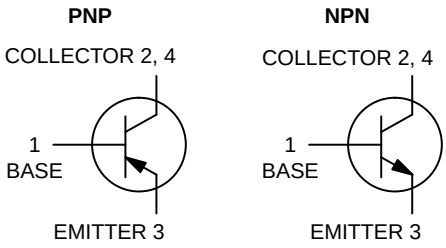
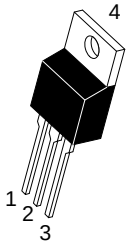
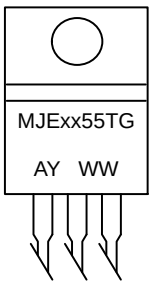
**10 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60 VOLTS − 75 WATTS**




**TO−220**
**CASE 221A−09**
**STYLE 1**

**MARKING DIAGRAM**




MJExx55T = Device Code
xx = 29 or 30
G = Pb−Free Package
A = Assembly Location
Y = Year
WW = Work Week

**ORDERING INFORMATION**

| Device | Package | Shipping |
|---|---|---|
| MJE2955TG | TO−220<br>(Pb−Free) | 50 Units / Rail |
| MJE3055TG | TO−220<br>(Pb−Free) | 50 Units / Rail |

**ELECTRICAL CHARACTERISTICS** ($T_C$ = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | |
| Collector−Emitter Sustaining Voltage (Note 2)<br>($I_C$ = 200 mAdc, $I_B$ = 0) | $V_{CEO(sus)}$ | 60 | − | Vdc |
| Collector Cutoff Current<br>($V_{CE}$ = 30 Vdc, $I_B$ = 0) | $I_{CEO}$ | − | 700 | μAdc |
| Collector Cutoff Current<br>($V_{CE}$ = 70 Vdc, $V_{EB(off)}$ = 1.5 Vdc)<br>($V_{CE}$ = 70 Vdc, $V_{EB(off)}$ = 1.5 Vdc, $T_C$ = 150°C) | $I_{CEX}$ | −<br>− | 1.0<br>5.0 | mAdc |
| Collector Cutoff Current<br>($V_{CB}$ = 70 Vdc, $I_E$ = 0)<br>($V_{CB}$ = 70 Vdc, $I_E$ = 0, $T_C$ = 150°C) | $I_{CBO}$ | −<br>− | 1.0<br>10 | mAdc |
| Emitter Cutoff Current<br>($V_{BE}$ = 5.0 Vdc, $I_C$ = 0) | $I_{EBO}$ | − | 5.0 | mAdc |
| **ON CHARACTERISTICS** | | | | |
| DC Current Gain (Note 2)<br>($I_C$ = 4.0 Adc, $V_{CE}$ = 4 0 Vdc)<br>($I_C$ = 10 Adc, $V_{CE}$ = 4.0 Vdc) | $h_{FE}$ | 20<br>5.0 | 100<br>− | − |
| Collector−Emitter Saturation Voltage (Note 2)<br>($I_C$ = 4.0 Adc, $I_B$ = 0.4 Adc)<br>($I_C$ = 10 Adc, $I_B$ = 3.3 Adc) | $V_{CE(sat)}$ | −<br>− | 1.1<br>8.0 | Vdc |
| Base−Emitter On Voltage (Note 2)<br>($I_C$ = 4.0 Adc, $V_{CE}$ = 4.0 Vdc) | $V_{BE(on)}$ | − | 1.8 | Vdc |
| **DYNAMIC CHARACTERISTICS** | | | | |
| Current−Gain−Bandwidth Product<br>($I_C$ = 500 mAdc, $V_{CE}$ = 10 Vdc, f = 500 kHz) | $f_T$ | 2.0 | − | MHz |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 20%.

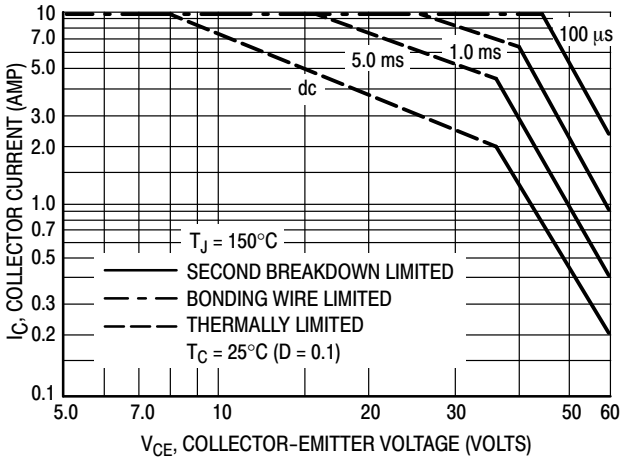



**Figure 1. Active−Region Safe Operating Area**

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)}$ = 150°C. $T_C$ is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150°C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

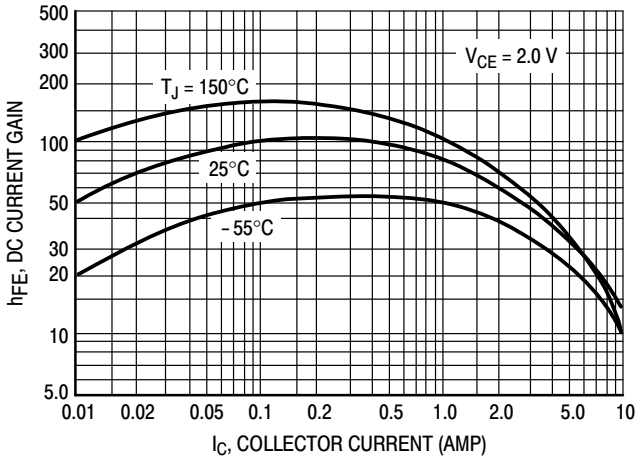



**Figure 2. DC Current Gain**

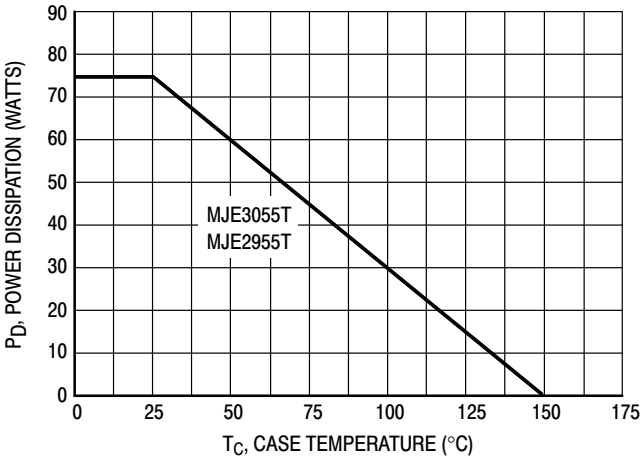



**Figure 3. Power Derating**

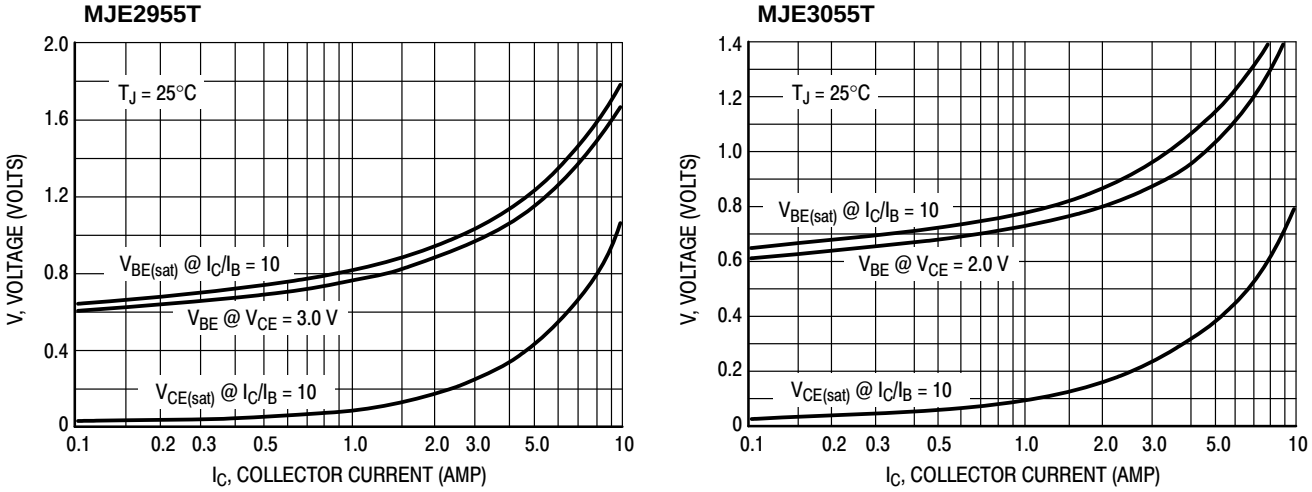
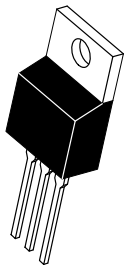



**Figure 4. “On” Voltages**

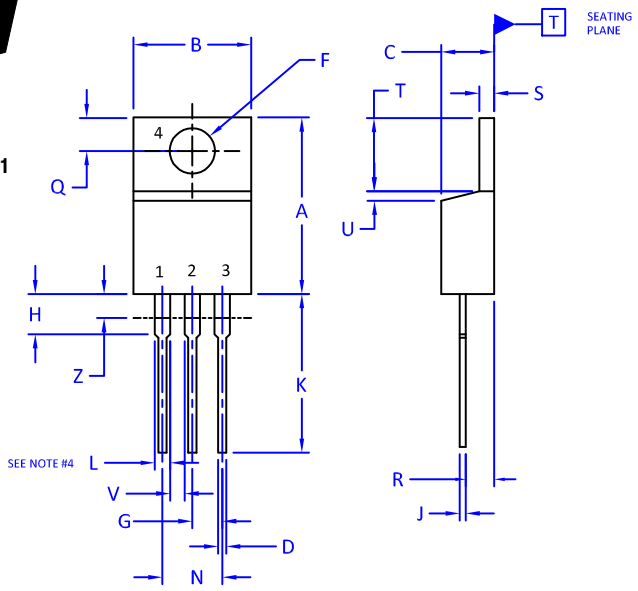
# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

**TO−220**
CASE 221A
ISSUE AK

DATE 13 JAN 2022



SCALE 1:1




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

| | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| DIM | MIN. | MAX. | MIN. | MAX. |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.415 | 9.66 | 10.53 |
| C | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.60 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.41 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | ---- | 1.15 | --- |
| Z | ---- | 0.080 | --- | 2.04 |

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

| | | |
|---|---|---|
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